

FIG. 1

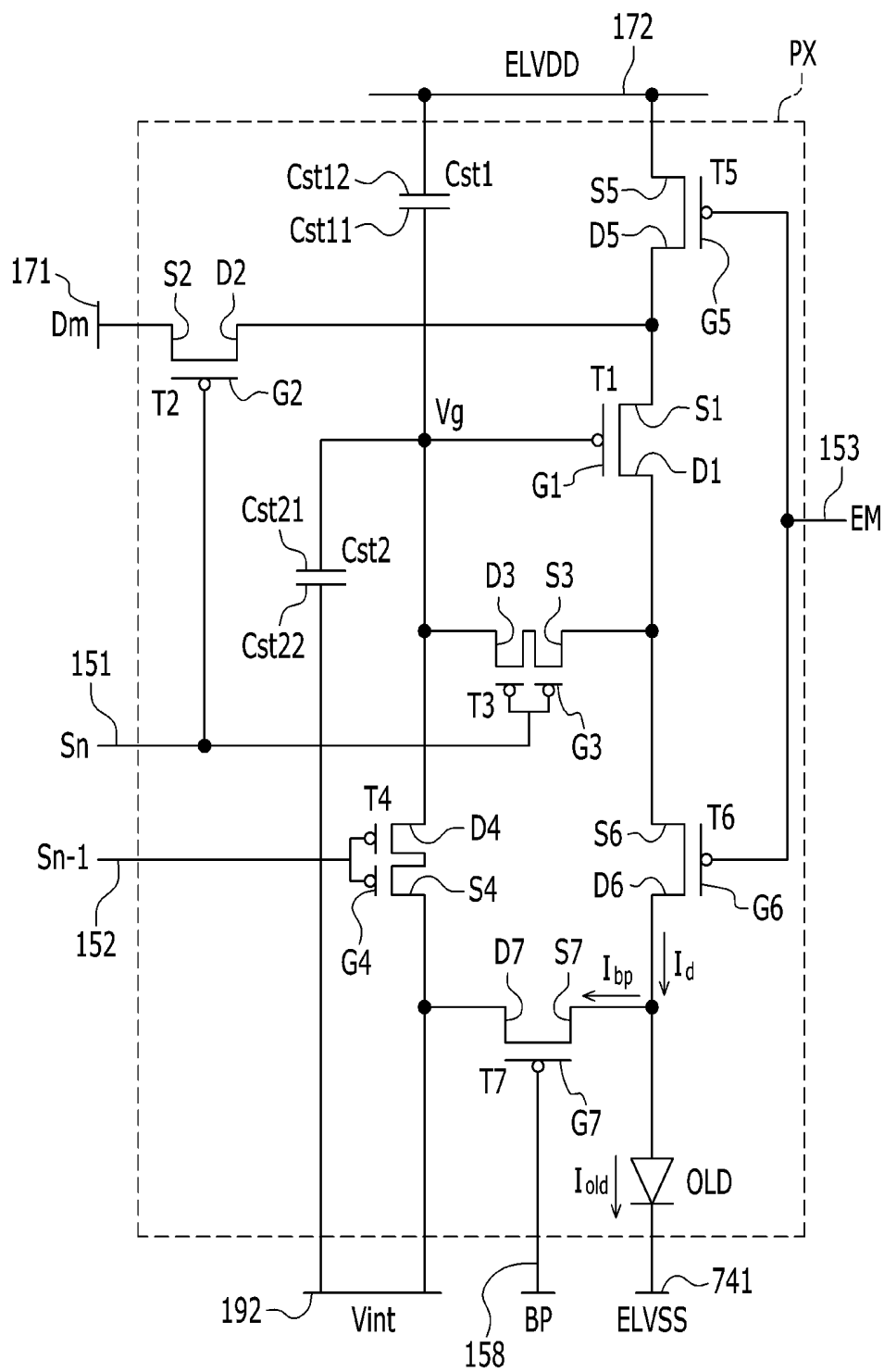


FIG. 2

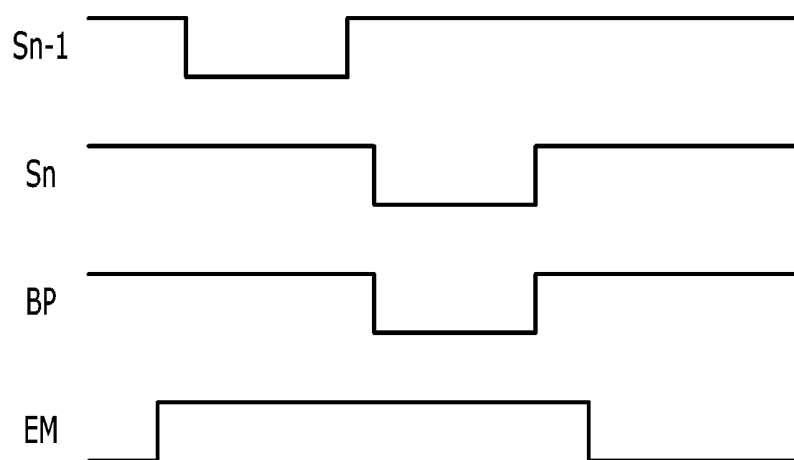


FIG. 3

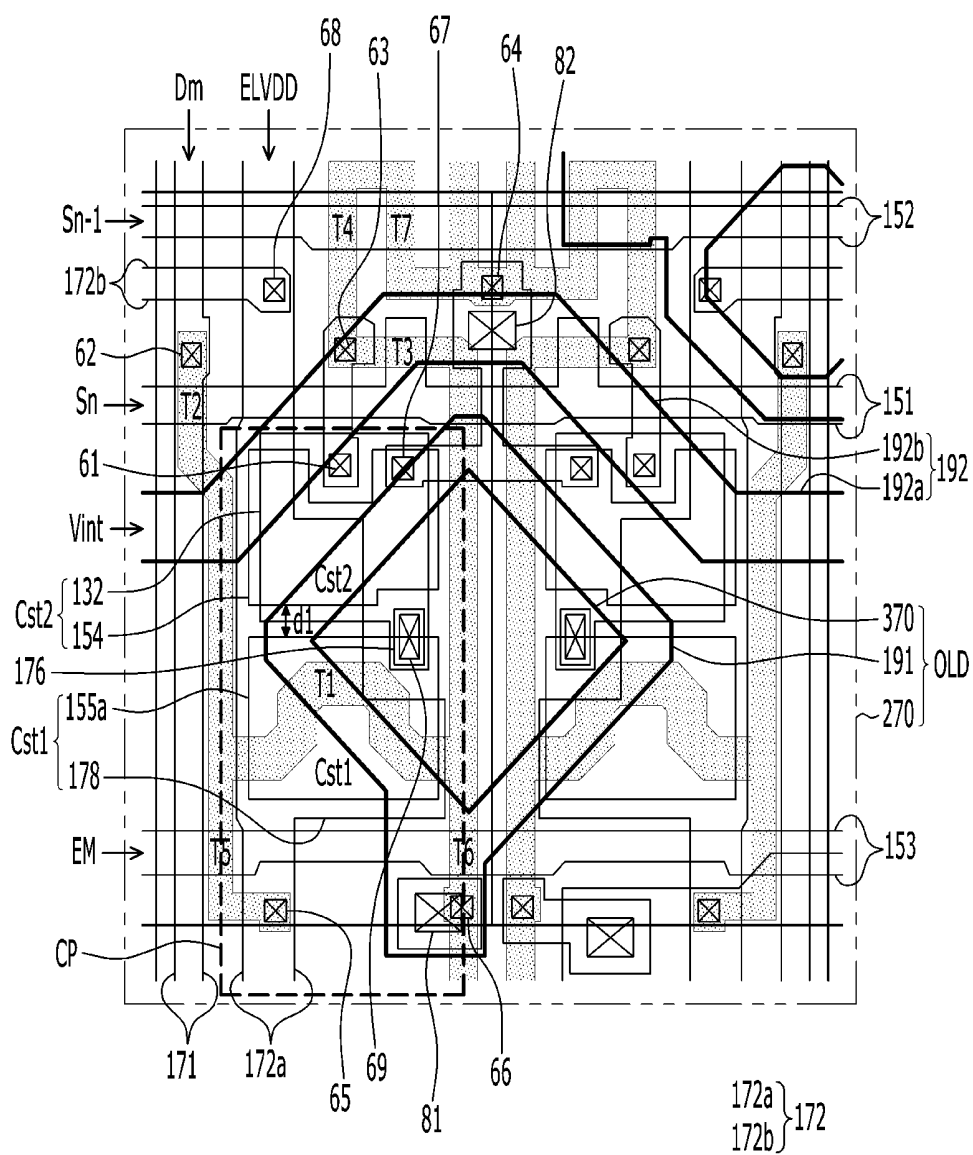


FIG. 4

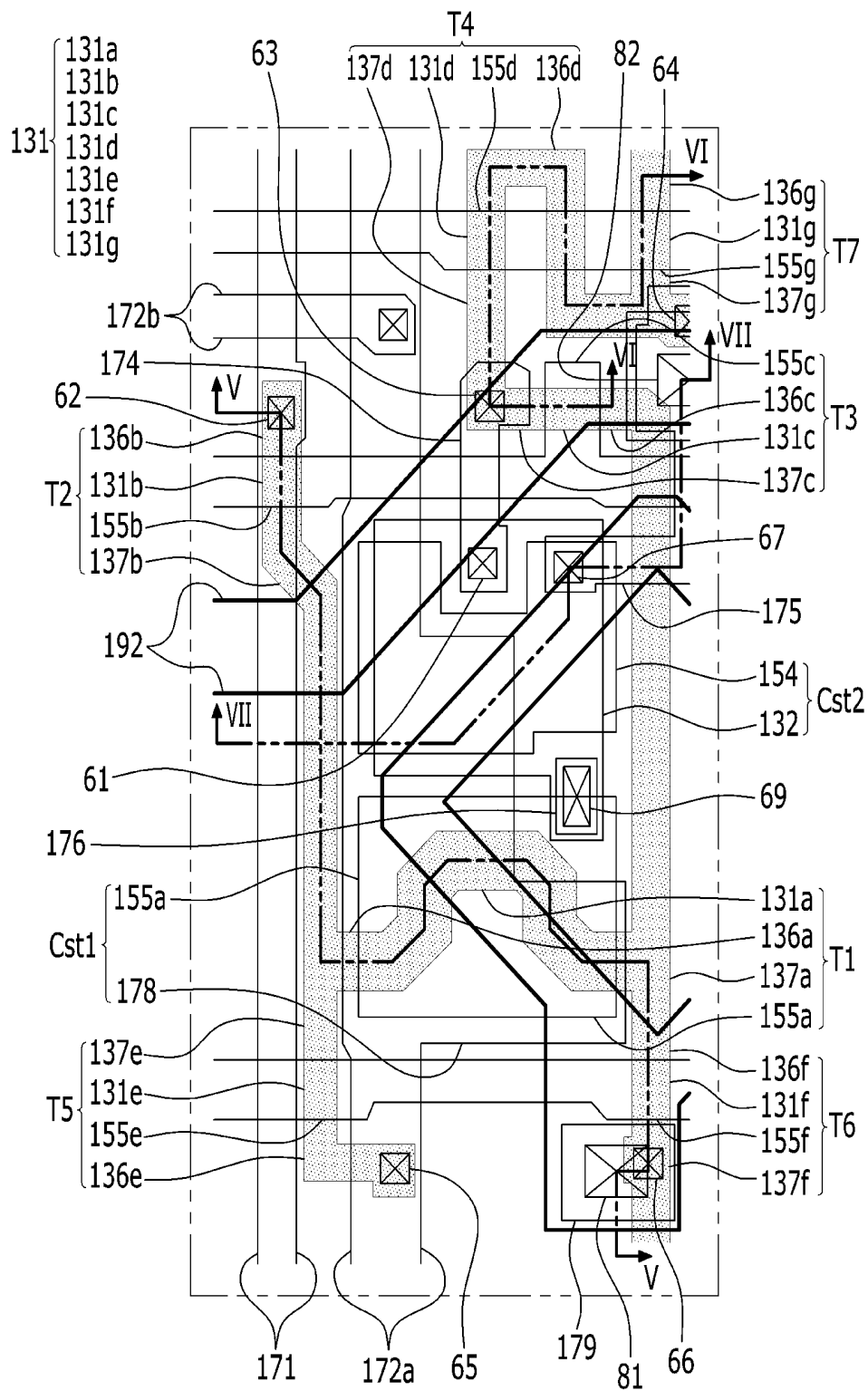


FIG. 6

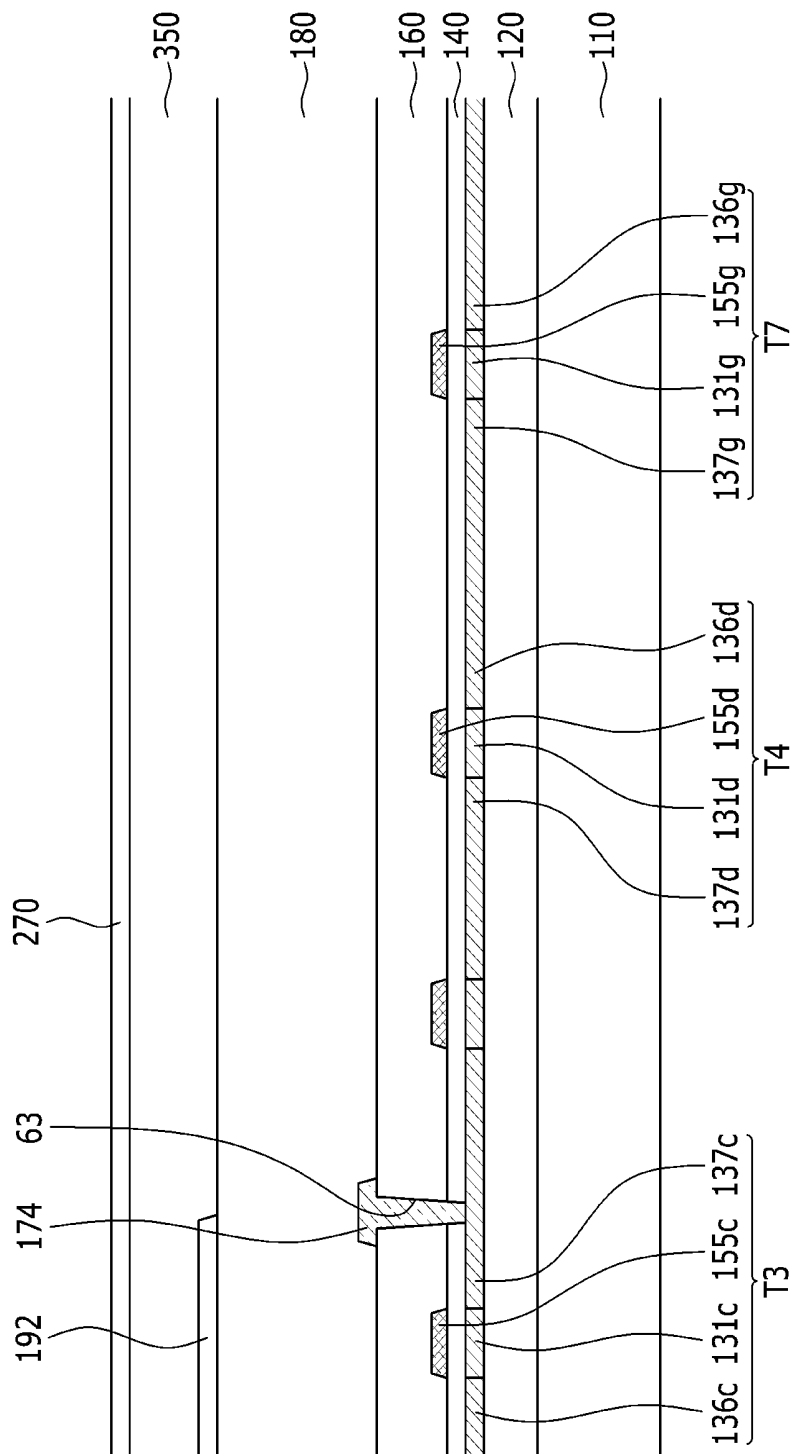


FIG. 7

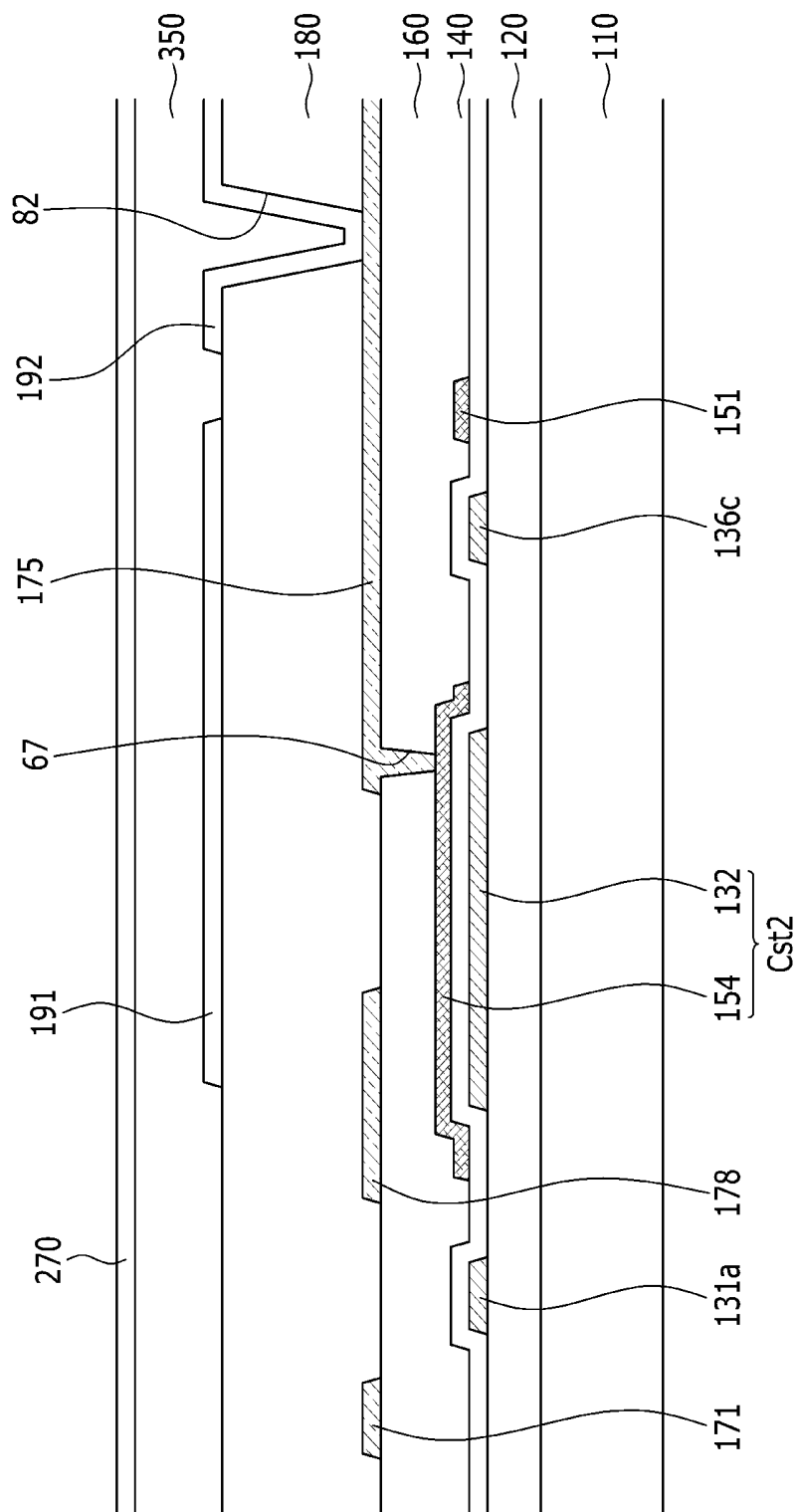
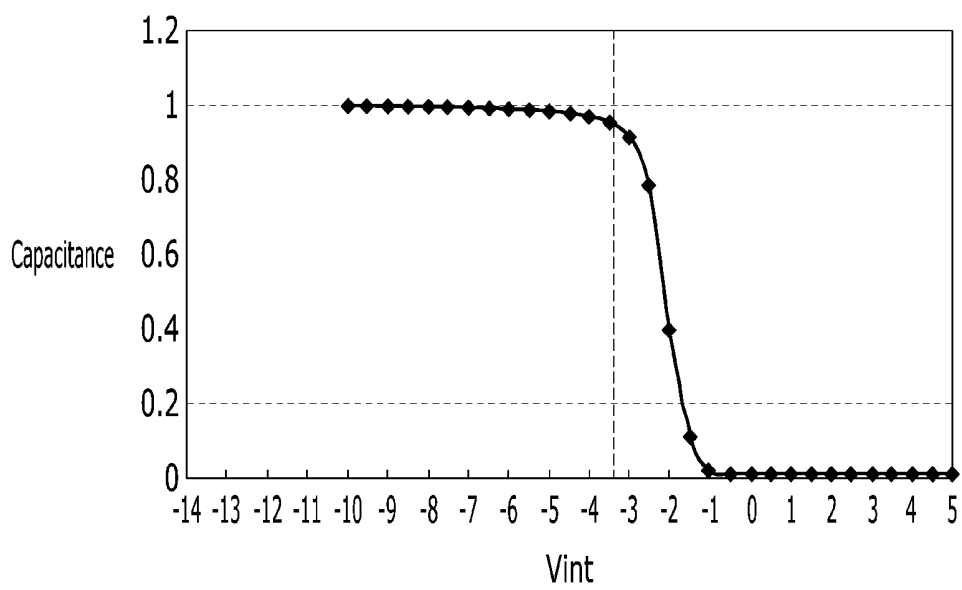


FIG. 8



ORGANIC LIGHT-EMITTING DIODE DISPLAY

CROSS-REFERENCE TO RELATED APPLICATION

This application claims priority to and the benefit of Korean Patent Application No. 10-2015-0059995 filed in the Korean Intellectual Property Office on Apr. 28, 2015, the entire contents of which are incorporated herein by reference.

BACKGROUND

Field

The described technology generally relates to an organic light-emitting diode display.

Description of the Related Technology

An organic light-emitting diode (OLED) includes two electrodes and an interposed organic light emitting layer. Electrons injected from a cathode electrode and holes injected from an anode electrode are bonded to each other in the organic light emitting layer to form excitons. Light is emitted when the excitons discharge energy.

OLED displays include a matrix of pixels including an OLED formed of the cathode, the anode, and the organic light emitting layer. A plurality of thin film transistors and capacitors for driving the OLED are formed in each pixel, or pixel circuit. The transistors generally include a switching transistor and a driving transistor.

The capacitor includes a storage capacitor overlapping the driving transistor, and since the size of the pixel decreases with increased display resolution, storage capacitance of the storage capacitor also decreases.

The above information disclosed in this Background section is only to enhance the understanding of the background of the disclosure, and therefore it can contain information that does not form the prior art that is already known in this country to a person of ordinary skill in the art.

SUMMARY OF CERTAIN INVENTIVE ASPECTS

One inventive aspect relates to an OLED display that can maximize storage capacitance in a high resolution structure.

Another aspect is an OLED display that includes a substrate; a plurality of scan lines formed on the substrate and transmitting a scan signal; a plurality of data lines crossing the plurality of scan lines and transmitting a data voltage; a plurality of driving voltage lines crossing the plurality of scan lines and transmitting a driving voltage; a switching transistor connected to the plurality of scan lines and the plurality of data lines; a driving transistor connected to the switching transistor and including a driving gate electrode and a driving channel overlapping each other; a first storage capacitor overlapping the driving channel and including a portion of the driving voltage line; a second storage capacitor separated from the first storage capacitor and overlapping a portion of the driving voltage line; and an OLED electrically connected to the driving transistor.

The first storage capacitor can include a first lower storage electrode as a driving gate electrode, and a first upper storage electrode that overlaps the first lower storage electrode and is a portion of the driving voltage line.

The second storage capacitor can include a second lower storage electrode formed with the same layer as the driving channel, and a second upper storage electrode overlapping

the second lower storage electrode and formed in the same layer as the first lower storage electrode.

The first lower storage electrode and the second upper storage electrode can be separated from each other.

The first lower storage electrode can be formed in the same layer as the scan line.

A storage connecting member formed in the same layer as the driving voltage line and connecting the first lower storage electrode and the second lower storage electrode to each other can be further included.

The OLED can include a pixel electrode electrically connected to the driving transistor, an organic emission layer formed on the pixel electrode, and a common electrode formed on the organic emission layer, and an initialization voltage line formed in the same layer as the pixel electrode and transmitting an initialization voltage initializing the driving transistor, and an initialization connecting member connecting the initialization voltage line and the second upper storage electrode to each other can be further included.

A gate insulating layer formed on the substrate, and an interlayer insulating layer covering the first lower storage electrode and the second upper storage electrode formed on the gate insulating layer can be further included, and the storage connecting member and the initialization connecting member can be formed on the interlayer insulating layer.

The storage connecting member can further include a contact hole connecting the first lower storage electrode and the second lower storage electrode to each other.

A thickness of the gate insulating layer can be thinner than the thickness of the interlayer insulating layer.

The driving channel can be formed on the substrate and the driving channel can be a curved plane.

The driving voltage line can include a first driving voltage line parallel to the data line and a second driving voltage line crossing the data line, and the first driving voltage line can be formed in the same layer as the data line, and the second driving voltage line can be formed in the same layer as the scan line.

The first storage capacitor and the second storage capacitor can be formed inside an imaginary rectangle shape formed by crossing the plurality of scan lines and the plurality of data lines.

The driving transistor can further include a driving source electrode and a driving drain electrode positioned at both sides of the driving channel.

A compensation transistor turned on depending on a scan signal, formed to compensate a threshold voltage of the driving transistor, and connected to the driving drain electrode, and a driving connecting member connecting a compensation drain electrode of the compensation transistor and the driving gate electrode can be further included.

Another aspect is an organic light-emitting diode (OLED) display, comprising: a substrate; a scan line formed over the substrate and configured to provide a scan signal; a data line crossing the scan line and configured to provide a data voltage; a driving voltage line crossing the scan line and configured to provide a driving voltage; a switching transistor electrically connected to the scan line and the data line; a driving transistor electrically connected to the switching transistor and including a driving gate electrode and a driving channel overlapping each other in the depth dimension of the OLED display; a first storage capacitor overlapping the driving channel in the depth dimension and including a portion of the driving voltage line; a second storage capacitor separated from the first storage capacitor and

overlapping the portion of the driving voltage line in the depth dimension; and an OLED electrically connected to the driving transistor.

In the above OLED display, the first storage capacitor includes i) a first lower storage electrode including the driving gate electrode and ii) a first upper storage electrode overlapping the first lower storage electrode and including the portion of the driving voltage line.

In the above OLED display, the second storage capacitor includes i) a second lower storage electrode formed on the same layer as the driving channel and ii) a second upper storage electrode overlapping the second lower storage electrode in the depth dimension and formed on the same layer as the first lower storage electrode.

In the above OLED display, the first lower storage electrode and the second upper storage electrode are separated from each other.

In the above OLED display, the first lower storage electrode is formed on the same layer as the scan line.

The above OLED display further comprises a storage connector formed on the same layer as the driving voltage line and configured to electrically connect the first lower storage electrode to the second lower storage electrode.

In the above OLED display, the OLED includes a pixel electrode electrically connected to the driving transistor, an organic emission layer formed over the pixel electrode, and a common electrode formed over the organic emission layer, wherein the OLED display further comprises: an initialization voltage line formed on the same layer as the pixel electrode and configured to provide an initialization voltage to initialize the driving transistor; and an initialization connector configured to electrically connect the initialization voltage line to the second upper storage electrode.

The above OLED display further comprises: a gate insulating layer formed over the substrate; and an interlayer insulating layer at least partially covering the first lower storage electrode and the second upper storage electrode formed over the gate insulating layer, wherein the storage connector and the initialization connector are formed over the interlayer insulating layer.

In the above OLED display, the storage has a contact hole configured to electrically connect the first lower storage electrode to the second lower storage electrode.

In the above OLED display, the gate insulating layer is thinner than the interlayer insulating layer.

In the above OLED display, the driving channel is formed over the substrate, wherein the driving channel is non-linear.

In the above OLED display, the driving voltage line includes i) a first driving voltage line substantially parallel to the data line and ii) a second driving voltage line crossing the data line, wherein the first driving voltage line is formed on the same layer as the data line, and wherein the second driving voltage line is formed on the same layer as the scan line.

In the above OLED display, the first and second storage capacitors are spaced apart from each other within a pixel of the OLED display.

In the above OLED display, the driving transistor further includes a driving source electrode and a driving drain electrode located at opposing ends of the driving channel.

The above OLED display further comprises: a compensation transistor electrically connected to the driving drain electrode and configured to be turned on based on a scan signal so as to compensate a threshold voltage of the driving transistor; and a driving connector configured to electrically connect a compensation drain electrode of the compensation transistor to the driving gate electrode.

Another aspect is an organic light-emitting diode (OLED) display comprising: a substrate; a data line formed over the substrate and configured to provide a data voltage; a driving voltage line formed adjacent to the data line and configured to provide a driving voltage; a first storage capacitor including a first upper storage electrode including a portion of the driving voltage line; and a second storage capacitor electrically separated from the first storage capacitor and overlapping the portion of the driving voltage line in the depth dimension of the OLED display.

The above OLED display further comprises a driving transistor including a driving gate electrode and a driving channel overlapping each other in the depth dimension, wherein the first storage capacitor overlaps the driving transistor in the depth dimension.

In the above OLED display, the first storage capacitor further includes a first lower storage electrode including the driving gate electrode, wherein the second storage capacitor includes i) a second lower storage electrode formed on the same layer as the driving channel and ii) a second upper storage electrode overlapping the second lower storage electrode in the depth dimension and formed on the same layer as the first lower storage electrode.

The above OLED display further comprises an OLED including a pixel electrode formed over the first upper and lower storage electrodes and the second upper and lower storage electrodes.

In the above OLED display, the first and second capacitors partially overlap each other.

According to at least one of the disclosed embodiments, the first storage capacitor and the second storage capacitor are formed in one pixel, thereby maximizing the storage capacitance.

Also, the first upper storage electrode is formed in the same layer and of the same material as the driving voltage line and the data line, thereby reducing at least one mask.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is an equivalent circuit diagram of a pixel of an OLED display according to an exemplary embodiment of the present disclosure.

FIG. 2 is a timing diagram of a signal applied to a pixel of an OLED display according to an exemplary embodiment of the present disclosure.

FIG. 3 is a schematic view of a plurality of transistors and capacitors of an OLED display according to an exemplary embodiment of the present disclosure.

FIG. 4 is a detailed layout view of FIG. 3.

FIG. 5 is a cross-sectional view of the OLED display of FIG. 4 taken along line V-V.

FIG. 6 is a cross-sectional view of the OLED display of FIG. 4 taken along line VI-VI.

FIG. 7 is a cross-sectional view of the OLED display of FIG. 4 taken along line VII-VII.

FIG. 8 is a graph of a second storage capacitance depending on an initialization voltage applied to a second storage capacitor of an OLED display according to an exemplary embodiment of the present disclosure.

DETAILED DESCRIPTION OF CERTAIN INVENTIVE EMBODIMENTS

The present disclosure will be described more fully hereinafter with reference to the accompanying drawings, in which exemplary embodiments of the disclosure are shown. As those skilled in the art would realize, the described

embodiments can be modified in various different ways, all without departing from the spirit or scope of the present disclosure.

In order to clearly describe the present disclosure, portions that are not connected with the description will be omitted. Like reference numerals designate like elements throughout the specification.

In addition, the size and thickness of each configuration shown in the drawings are arbitrarily shown for understanding and ease of description, but the present disclosure is not necessarily limited thereto. In the drawings, the thickness of layers, films, panels, regions, etc., are exaggerated for clarity. In the drawings, the thickness of layers, films, panels, regions, etc., are also exaggerated for ease of description.

In addition, unless explicitly described to the contrary, the word “comprise” and variations such as “comprises” or “comprising”, will be understood to imply the inclusion of stated elements but not the exclusion of any other elements. Further, it will be understood that when an element such as a layer, film, region, or substrate is referred to as being “on” another element, it can be directly on the other element or intervening elements can also be present. Further, in the specification, the word “on” means positioning on or below the object portion, but does not necessarily mean positioning on the upper side of the object portion based on a gravitational direction.

Further, in the specification, the word “in plan view” means when an object portion is viewed from above, and the word “in cross section” means when a cross section taken by vertically cutting an object portion is viewed from the side.

Further, the number of thin film transistors (TFTs) and capacitors is not limited to the number illustrated in the accompanying drawings and an OLED display can be formed in various structures in which one pixel can include a plurality of transistors and at least one capacitor and is further provided with a separate wiring or does not include the existing wirings. Here, a pixel means a minimum unit which displays an image, and the organic light emitting device displays an image through a plurality of pixels. In this disclosure, the term “substantially” includes the meanings of completely, almost completely or to any significant degree under some applications and in accordance with those skilled in the art. The term “connected” can include an electrical connection.

Hereinafter, an OLED display according to an exemplary embodiment of the present disclosure will be described with reference to the accompanying drawings.

FIG. 1 is an equivalent circuit diagram of a pixel of an OLED display according to an exemplary embodiment of the present disclosure.

As shown in FIG. 1, the OLED display includes a plurality of signal lines 151, 152, 153, 158, 171, 172, and 192, and a plurality of pixels PX arranged in a matrix and connected to the plurality of signal lines.

One pixel PX includes a plurality of transistors T1, T2, T3, T4, T5, T6, and T7, a first storage capacitor Cst1, a second storage capacitor Cst2, and an OLED (OLD) that are connected to the signal lines 151, 152, 153, 158, 171, 172, and 192.

The transistors T1, T2, T3, T4, T5, T6, and T7 include a driving transistor T1, a switching transistor T2, a compensation transistor T3, an initialization transistor T4, an operation control transistor T5, a light emission control transistor T6, and a bypass transistor T7.

The signal lines 151, 152, 153, 158, 171, 172, and 192 include a scan line 151 which transfers a scan signal Sn, a front end scan line 152 which transfers a front end scan

signal Sn-1 to the initialization transistor T4, a light emission control line 153 which transfers a light emitting control signal EM to the operation control transistor T5 and the light emission control transistor T6, a bypass control layer 158 which transfers a bypass signal BP to the bypass transistor T7, a data line 171 which intersects the scan line 151 and transfers a data signal Dm, a driving voltage line 172 which transfers a driving voltage ELVDD and is formed approximately parallel to the data line 171, and an initialization voltage line 192 which transfers an initialization voltage Vint for initializing the driving transistor T1.

A gate electrode G1 of the driving transistor T1 is connected to one terminal Cst1 of the storage capacitor Cst, a source electrode S1 of the driving transistor T1 is connected to the driving voltage line 172 via the operation control transistor T5, and a drain electrode D1 of the driving transistor T1 is electrically connected to an anode of the OLED (OLD) via the light emission control transistor T6. The driving transistor T1 receives the data signal Dm depending on a switching operation of the switching transistor T2 to supply a driving current Id to the OLED (OLD).

A gate electrode G2 of the switching transistor T2 is connected to the scan line 151, a source electrode S2 of the switching transistor T2 is connected to the data line 171, and a drain electrode D2 of the switching transistor T2 is connected to the driving voltage line 172 via the operation control transistor T5, while being connected to the source electrode S1 of the driving transistor T1. The switching transistor T2 is turned on depending on the scan signal Sn which is transferred through the scan line 151 to perform a switching operation of transferring the data signal Dm transferred to the data line 171 to the source electrode S1 of the driving transistor T1.

A gate electrode G3 of the compensation transistor T3 is connected to the scan line 151, a source electrode S3 of the compensation transistor T3 is connected to the anode of the OLED (OLD) via the light emission transistor T6 while being connected to the drain electrode D1 of the driving transistor T1, and a drain electrode D3 of the compensation transistor T3 is connected to a drain electrode D4 of the initialization transistor T4, one terminal Cst1 of the storage capacitor Cst, and the gate electrode G1 of the driving transistor T1. The compensation transistor T3 is turned on depending on the scan signal Sn which is transferred through the scan line 151 to connect the gate electrode G1 and the drain electrode D1 of the driving transistor T1 so as to diode-connect the driving transistor T1.

A gate electrode G4 of the transistor T4 is connected to the front end scan line 152, the source electrode S4 of the initialization transistor T4 is connected to the initialization voltage line 192, and the drain electrode D4 of the initialization transistor T4 is connected to one terminal Cst1 of the first storage capacitor Cst1 via both the drain electrode D3 of the compensation transistor T3 and the gate electrode G1 of the driving transistor T1. The initialization transistor T4 is turned on depending on the front end scan signal Sn-1, which is transferred through the front end scan line 152 to transfer the initialization voltage Vint to the gate electrode G1 of the driving transistor T1 so as to perform the initialization operation, which initializes a gate voltage Vg of the gate electrode G1 of the driving transistor T1. In this case, the compensation transistor T3 and the initialization transistor T4 are configured of a transistor having a dual gate structure to cut off current leakage.

A gate electrode G5 of the operation control transistor T5 is connected to the light emission control line 153, the source electrode S5 of the operation control transistor T5 is

connected to the driving voltage line **172**, and the drain electrode **D5** of the operation control transistor **T5** is connected to the source electrode **S1** of the driving transistor **T1** and the drain electrode **S2** of the switching transistor **T2**.

A gate electrode **G6** of the light emission transistor **T6** is connected to the light emission control line **153**, a source electrode **S6** of the light emission transistor **T6** is connected to the drain electrode **D1** of the driving transistor **T1** and the source electrode **S3** of the compensation transistor **T3**, and a drain electrode **D6** of the light emission transistor **T6** is electrically connected to the anode of the OLED (OLD). The operation control transistor **T5** and the light emission control transistor **T6** are simultaneously (or concurrently) turned on depending on the light emission control signal **EM**, which is transferred through the light emission control line **153**, and thus the driving voltage **ELVDD** is compensated by the diode-connected driving transistor **T1** and then is transferred to the OLED (OLD).

A gate electrode **G7** of the bypass transistor **T7** is connected to the bypass control line **158**, a source electrode **S7** of the bypass transistor **T7** is connected to both the drain electrode **D6** of the light emission control transistor **T6** and the anode of the OLED (OLD), and a drain electrode **D7** of the bypass transistor **T7** is connected to both the initialization voltage line **192** and the source electrode **S4** of the initialization transistor **T4**.

The other terminal **Cst12** of the capacitor **Cst1** is connected to the driving voltage line **172** and a cathode of the OLED (OLD) is connected to the common voltage line **741** through which a common voltage **ELVSS** is transferred.

One end **Cst21** of the second storage capacitor **Cst2** is connected to both the gate electrode **G1** of the driving transistor **T1** and one end **Cst11** of the first storage capacitor **Cst1**, and the other end **Cst22** of the second storage capacitor **Cst2** is connected to the initialization voltage line **192**.

Meanwhile, in the exemplary embodiment of the present disclosure, the seven-transistor and two-capacitor structure including the bypass transistor **T7** is illustrated, but the present disclosure is not limited thereto, and the number of transistors and the number of capacitors can vary.

Hereinafter, a detailed operation process of one pixel of the OLED display according to the exemplary embodiment of the present disclosure will be described in detail with reference to FIG. 2.

FIG. 2 is a timing diagram of a signal applied to a pixel of an OLED display according to an exemplary embodiment of the present disclosure.

As illustrated in FIG. 2, the previous scan signal **Sn-1** of a low level is supplied through the previous scan line **152** for an initialization period. Next, the initialization transistor **T4** is turned on depending on the low-level front end scan signal **Sn-1**, the initialization voltage **Vint** is connected to the gate electrode **G1** of the driving transistor **T1** from the initialization voltage line **192** through the initialization transistor **T4**, and the driving transistor **T1** is initialized by the initialization voltage **Vint**.

Next, the low-level scan signal **Sn** is supplied through the scan line **151** for a data programming period. Next, the switching transistor **T2** and the compensation transistor **T3** are turned on depending on the low-level scan signal **Sn**. In this case, the driving transistor **T1** is diode-connected by the turned on compensation transistor **T3** and is forward biased.

Next, a compensation voltage **Dm+Vth** (**Vth** is a negative value) which is reduced by as much as a threshold voltage (**Vth**) of the driving transistor **T1** from the data signal **Dm** supplied from the data line **171** is applied to the gate electrode **G1** of the driving transistor **T1**. That is, the gate

voltage **Vg** which is applied to the gate electrode **G1** of the driving transistor **T1** is the compensation voltage **Dm+Vth**.

The driving voltage **ELVDD** and the compensation voltage **Dm+Vth** is applied to both terminals of the storage capacitor **Cst** and a charge corresponding to the difference in voltage between both terminals of the storage capacitor **Cst** is stored in the first storage capacitor **Cst1**.

Next, the light control signal **EM** supplied from the light emission control line **153** is changed from a high level to a low level for a light emission period. Next, the operation control transistor **T5** and the light control transistor **T6** are turned on by the low-level light emission control signal **Em** for the light emission period.

Next, a driving current **Id** corresponding to a voltage difference between the gate voltage **Vg** of the gate electrode **G1** of the driving transistor **T1** and the driving voltage **ELVDD** is generated and the driving current **Id** is supplied to the OLED (OLD) through the light emission control transistor **T6**. A driving gate-source voltage **Vgs** of the driving transistor **T1** is maintained at '**(Dm+Vth)-ELVDD**' by the storage capacitor **Cst** for the light emission period and depending on a current-voltage relationship of the driving transistor **T1**, the driving current **Id** is proportional to a square '**(Dm-ELVDD)²**' of a value obtained by subtracting the threshold voltage from the driving gate-source voltage **Vgs**. Therefore, the driving current **Id** is determined independent of the threshold voltage **Vth** of the driving transistor **T1**.

In this case, the bypass transistor **T7** receives a bypass signal **BP** from the bypass control line **158**. Accordingly, the driving current **Id** is partially discharged through the bypass transistor **T7** as a bypass current **Ibp**.

When the OLED (OLD) emits light even though a minimum current of the driving transistor **T1** displaying a black image flows as a driving current, the black image is not properly displayed. Therefore, the bypass transistor **T7** can disperse some of the minimum current of the driving transistor **T1** to current paths other than a current path to the OLED as the bypass current **Ibp**. Here, the minimum current of the driving transistor **T1** means a current under the condition that the driving gate-source voltage **Vgs** of the driving transistor **T1** is smaller than the threshold voltage **Vth**, and thus the driving transistor **T1** is turned off. The minimum driving current (e.g., a current which is equal to or less than about 10 pA) under the condition that the driving transistor **T1** is turned off is transferred to the OLED (OLD) and is represented by an image of black luminance. When the minimum driving current representing the black image flows, the effects of the bypass transfer of the bypass current **Ibp** is large, but when a large driving current representing an image like a general image or a white image flows, an effect of the bypass current **Ibp** can be minimal. Therefore, when the driving current representing the black image flows, a light emitting current **Iold** of the OLED (OLD), which is reduced by as much as a current amount of the bypass current **Ibp** which exits from the driving current **Id** through the bypass transistor **T7**, has a minimum current amount is at a level to certainly represent the black image. Therefore, the accurate black luminance image is achieved by using the bypass transistor **T7** to improve a contrast ratio. In FIG. 2, the bypass signal **BP** is the same as the previous scan signal **Sn-1**, but is not necessarily limited thereto.

Next, the detailed structure of the outermost pixel **PX2** among the plurality of pixels of the OLED display illustrated in FIG. 1 and FIG. 2 will be described in detail with reference to FIG. 3, FIG. 4, FIG. 5, FIG. 6, and FIG. 7.

FIG. 3 is a schematic view of a plurality of transistors and capacitors of an OLED display according to an exemplary embodiment of the present disclosure. FIG. 4 is a detailed layout view of FIG. 3. FIG. 5 is a cross-sectional view of the OLED display of FIG. 4 taken along line V-V. FIG. 6 is a cross-sectional view of the OLED display of FIG. 4 taken along line VI-VI. FIG. 7 is a cross-sectional view of the OLED display of FIG. 4 taken along line VII-VII.

Hereinafter, the detailed plane structure of the OLED display according to the exemplary embodiment of the present disclosure will first be described with reference to FIG. 3 and FIG. 4, and the detailed section structure will be described with reference to FIG. 5, FIG. 6, and FIG. 7.

As shown in FIG. 3 and FIG. 4, the OLED display according to an exemplary embodiment of the present disclosure includes a scan line 151, a previous scan line 152, an emission control line 153, and a bypass control line 158, which respectively transmit a scan signal Sn, a previous scan signal Sn-1, an emission control signal EM, and a bypass signal BP to the pixel PX and are formed along a row direction. A data line 171 and a driving voltage line 172, which intersect the scan line 151, the previous scan line 152, the light emission control line 153, and the bypass control line 158 and apply the data signal Dm and the driving voltage ELVDD to the pixel 1, are included. The driving voltage line 172 includes a first driving voltage line 172a parallel to the data line 171 and a second driving voltage line 172b parallel to the scan line 151. The first driving voltage line 172a and the second driving voltage line 172b are connected through the contact hole 68. Accordingly, compared to the case in which the first driving voltage line 172a is only formed to extend in a vertical direction to transmit the driving voltage, an exemplary embodiment of the present disclosure connects the first driving voltage line 172a elongated in a vertical direction and the second driving voltage line 172b elongated in a horizontal direction through the contact hole 68 to be a mesh structure, thereby minimizing the voltage drop of the driving voltage line 172.

The initialization voltage Vint is transferred from the initialization voltage line 192 to the compensation transistor T3 via the initialization transistor T4. The initialization voltage line 192 alternately includes a straight portion and an oblique portion. The straight portion 192a is formed to be parallel to the scan line 121 and the oblique portion 192b extends at a predetermined angle to the straight portion 192a.

Further, the pixel PX is provided with the driving transistor T1, the switching transistor T2, the compensation transistor T3, the initialization transistor T4, the operation control transistor T5, the light emission control transistor T6, the bypass transistor T7, the first storage capacitor Cst1, the second storage capacitor Cst2, and the OLED (OLD).

The OLED (OLD) includes a pixel electrode 191, an organic emission layer 370, and a common electrode 270. In this case, the compensation transistor T3 and the initialization transistor T4 are configured of a transistor having a dual gate structure to cut off current leakage.

Each channel of the driving transistor T1, the switching transistor T2, the compensation transistor T3, the initialization transistor T4, the operation control transistor T5, the light emission control transistor T6, and the bypass transistor T7 is formed inside one connected semiconductor 130, which can be bent in various shapes. The semiconductor 130 can be formed of polysilicon or an oxide semiconductor. The oxide semiconductor can include one of titanium (Ti), hafnium (Hf), zirconium (Zr), aluminum (Al), tantalum (Ta), germanium (Ge), zinc (Zn), gallium (Ga), tin (Sn), or indium

(In), zinc oxide (ZnO), indium-gallium-zinc oxide (In-GaZnO4), indium zinc oxide (Zn-In-O), zinc-tin oxide (Zn-Sn-O), indium gallium oxide (In-Ga-O), indium-tin oxide (In-Sn-O), indium-zirconium oxide (In-Zr-O), indium-zirconium-zinc oxide (In-Zr-Zn-O), indium-zirconium-tin oxide (In-Zr-Sn-O), indium-zirconium-gallium oxide (In-Zr-Ga-O), indium-aluminum oxide (In-Al-O), indium-zinc-aluminum oxide (In-Zn-Al-O), indium-tin-aluminum oxide (In-Sn-Al-O), indium-aluminum-gallium oxide (In-Al-Ga-O), indium-tantalum oxide (In-Ta-O), indium-tantalum-zinc oxide (In-Ta-Zn-O), indium-tantalum-tin oxide (In-Ta-Sn-O), indium-tantalum-gallium oxide (In-Ta-Ga-O), indium-germanium oxide (In-Ge-O), indium-germanium-zinc oxide (In-Ge-Zn-O), indium-germanium-tin oxide (In-Ge-Sn-O), indium-germanium-gallium oxide (In-Ge-Ga-O), titanium-indium-zinc oxide (Ti-In-Zn-O), and hafnium-indium-zinc oxide (Hf-In-Zn-O), which are complex oxides thereof. In the case the semiconductor 130 is formed of an oxide semiconductor material, a separate passivation layer can be added for protecting the oxide semiconductor material which is vulnerable to external influences such as a high temperature.

The semiconductor 130 includes a channel which is doped with an N-type impurity or a P-type impurity, and a source doping part and a drain doping part which are formed at respective sides of the channel and doped with an opposite-type doping impurity compared to the doping impurity doped on the channel. In the exemplary embodiment, the source doping part and the drain doping part correspond to the source electrode and the drain electrode, respectively. The source electrode and the drain electrode formed in the semiconductor 130 can be formed by doping only the corresponding regions. Further, in the semiconductor 130, a region between source electrodes and drain electrodes of different transistors is doped, and thus the source electrode and the drain electrode can be electrically connected to each other.

As illustrated in FIG. 4, the channel 131 includes a driving channel 131a formed in the driving transistor T1, a switching channel 131b formed in the switching transistor T2, a compensation channel 131c formed in the compensation transistor T3, an initialization channel 131d formed in the initialization transistor T4, an operation control channel 131e formed in the operation control transistor T5, a light emission control channel 131f formed in the light emission control transistor T6, and a bypass channel 131g formed in the bypass transistor T7.

The driving transistor T1 includes the driving channel 131a, a driving gate electrode 155a, a driving source electrode 136a, and a driving drain electrode 137a. The driving channel 131a can be curved and can have a meandering shape or a zigzag shape. As such, by forming the curved driving channel 131a, the driving channel 131a can be formed to be elongated in a narrow space. Accordingly, a driving range of the driving gate-source voltage Vgs between the driving gate electrode 155a and the driving source electrode 136a is increased by the elongated driving channel 131a. Since the driving range of the gate voltage is increased, a gray scale of light emitted from the OLED OLD can be finely controlled by changing the magnitude of the gate voltage, and as a result, the resolution of the OLED display device can be enhanced and display quality can be improved. Various examples such as 'reverse S', 'S', 'M', and 'W' can be implemented by variously modifying the shape of the driving channel 131a.

The driving gate electrode **155a** overlaps the driving channel **131a**, and the driving source electrode **136a** and the driving drain electrode **137a** are formed at respective sides of the driving channel **131a** to be close. The driving gate electrode **155a** is connected to the first data connecting member (or first data connector) **174** through a contact hole **61**.

The switching transistor **T2** includes the switching channel **131b**, a switching gate electrode **155b**, a switching source electrode **136b**, and a switching drain electrode **137b**. The switching gate electrode **155b**, which is a part extending downward from the scan line **121**, overlaps the switching channel **131b**, and the switching source electrode **136b** and the switching drain electrode **137b** are formed at respective sides of the switching channel **131b** to be close thereto. The switching source electrode **136b** is connected to the data line **171** through a contact hole **62**.

The compensation transistor **T3** includes the compensation channel **131c**, a compensation gate electrode **155c**, a compensation source electrode **136c**, and a compensation drain electrode **137c**. The compensation gate electrode **155c**, which is a part of the scan line **151**, is formed in two in order to prevent current leakage, and it overlaps the compensation channel **131c**. The compensation source electrode **136c** and the compensation drain electrode **137c** are formed to be adjacent to respective sides of the compensation channel **131c**. The compensation drain electrode **137c** is connected to a driving connecting member (or driving connector) **174** through a contact hole **63**.

The initialization transistor **T4** includes the initialization channel **131d**, an initialization gate electrode **155d**, an initialization source electrode **136d**, and an initialization drain electrode **137d**. The initialization gate electrode **155d** that is a part of the previous scan line **152** is formed in two in order to prevent current leakage, and it overlaps the initialization channel **131d**. The initialization source electrode **136d** and the initialization drain electrode **137d** are formed to be adjacent to respective sides of the initialization channel **131d**. The initialization source electrode **136d** is connected to an initialization connecting member (or initialization connector) **175** through a contact hole **64**.

The operation control transistor **T5** includes the operation control channel **131e**, an operation control gate electrode **155e**, an operation control source electrode **136e**, and an operation control drain electrode **137e**. The operation control gate electrode **155e**, which is a part of the light emission control line **153**, overlaps the operation control channel **131e**, and the operation control source electrode **136e** and the operation control drain electrode **137e** are formed to be adjacent to respective sides of the operation control channel **131e**. The operation control source electrode **136e** is connected to a driving voltage line **172** through a contact hole **65**.

The light emission control transistor **T6** includes the light emission control channel **131f**, a light emission control gate electrode **155f**, a light emission control source electrode **136f**, and a light emission control drain electrode **137f**. The light emission control gate electrode **155f**, which is a part of the light emission control line **153**, overlaps the light emission control channel **131f**. The light emission control source electrode **136f** and the light emission control drain electrode **137f** are formed to be adjacent to respective sides of the light emission control channel **131f**. The light emission control drain electrode **137f** is connected to the third data connecting member (or third data connector) **179** through a contact hole **66**.

The bypass transistor **T7** includes the bypass channel **131g**, a bypass gate electrode **155g**, a bypass source electrode **136g**, and a bypass drain electrode **137g**. The bypass gate electrode **155g**, which is a part of the bypass control line **158**, overlaps the bypass channel **131g**, and the bypass source electrode **136g** and the bypass drain electrode **137g** are formed to be adjacent to respective sides of the bypass channel **131g**.

The bypass source electrode **136g** is directly connected to the light emission control drain electrode **137f**, and the bypass drain electrode **137g** is directly connected to the initialization source electrode **136d**.

One end of the driving channel **131a** of the driving transistor **T1** is connected to the switching drain electrode **137b** and the operation control drain electrode **137e**, and the other end of the driving channel **131a** is connected to the compensation source electrode **136c** and the light emission control source electrode **136f**.

The first storage capacitor **Cst1** includes a first lower storage electrode **155a** and a first upper storage electrode **178** formed via an interlayer insulating layer **160** interposed therebetween. The first lower storage electrode **155a** corresponds to the driving gate electrode **155a** and the first upper storage electrode **178** is an expansion of the first driving voltage line **172a**. Here, the gate insulating layer **160** becomes a dielectric material, and a storage capacitance is determined by a charge charged in the first storage capacitor **Cst1** and a voltage between the electrodes **155a** and **178**. As described above, by using the driving gate electrode **155a** as the first lower storage electrode **155a**, a space for forming the first storage capacitor can be obtained in the space that is decreased by the driving channel **131a** occupying a large area in the pixel.

The interlayer insulating layer **160** as the dielectric material of the first storage capacitor **Cst1** has a thickness of about 4000 Å, which is thicker than the thickness of about 1300 Å of the gate insulating layer **140**. Accordingly, the first storage capacitance is decreased compared to an 8 mask structure using the gate insulating layer **140** as the dielectric material.

However, in an exemplary embodiment of the present disclosure, to increase the storage capacitance, the second storage capacitor **Cst2** is formed at a position separated from the first storage capacitor **Cst1**. The first storage capacitor **Cst1** and the second storage capacitor **Cst2** are formed inside an imaginary rectangular shape **CP** formed by crossing the plurality of scan lines **151** and the data lines **171**.

The second storage capacitor **Cst2** includes a second lower storage electrode **132** and a second upper storage electrode **154** formed via the gate insulating layer **140**. The first lower storage electrode **155a** has a substantially rectangular shape and is separated from the second upper storage electrode **154** by a predetermined interval **dl**. Here, the gate insulating layer **140** becomes a dielectric material and a second storage capacitance is determined by the charge charged in the second storage capacitor **Cst2** and the voltage between both electrodes **132** and **154**.

The first lower storage electrode **155a** of the driving gate electrode **155a** is connected to the second lower storage electrode **132** through the contact hole **69**, and the second lower storage electrode **132** is connected to one end of the driving connecting member **174** through a storage groove **51** formed in the second upper storage electrode **154**. Accordingly, a contact hole **61** for connecting one end of the driving connecting member **174** and the second lower storage electrode **132** is formed inside the storage groove **51**.

The first upper storage electrode **178** is an expansion extending from the first driving voltage line **172a**. Accordingly, the first storage capacitor **Cst1** stores a first storage capacitance corresponding to a difference between the driving voltage ELVDD transmitted to the first upper storage electrode **178** through the driving voltage line **172** and the compensation voltage $Dm+V_{th}$ transmitted to the first lower storage electrode **155a** through the driving connecting member **174** and the second lower storage electrode **132**. As described above, by forming the portion of the driving voltage line **172** as the second storage electrode **178**, it is not necessary for the second storage electrode to be formed as a separate layer, and thus the number of masks used in manufacturing such can be reduced. In this case, a total of 7 masks are used from the semiconductor **130** to the common electrode **270**, and this manufacturing method is referred to as a 7 mask process, while the structure of the OLED display manufactured by the 7 mask process is referred to as a 7 mask structure.

Also, the second lower storage electrode **132** is separated from the driving channel **131a** on the plane and is positioned on the driving channel **131a**. The second lower storage electrode **132** is connected to the driving connecting member **174** through the contact hole **61**. The driving connecting member **174** is formed in the same layer as the data line **171** to be substantially parallel and the other end of the driving connecting member **174** is connected to the compensation drain electrode **137c** of the compensation transistor **T3** through the contact hole **63** and the initialization drain electrode **137d** of the initialization transistor **T4**. Accordingly, the driving connecting member **174** connects the driving gate electrode **155a**, the compensation drain electrode **137c** of the compensation transistor **T3**, and the initialization drain electrode **137d** of the initialization transistor **T4** to each other.

Also, the second upper storage electrode **154** is connected to the initialization connecting member **175** through the contact hole **67**, and the initialization connecting member **175** is connected to the initialization voltage line **192** through the contact hole **82**.

The second lower storage electrode **132** is formed of the semiconductor **130** and overlaps the second upper storage electrode **154** such that it is not doped with the doping impurity on the channel doping. In this case, when the initialization voltage V_{int} transmitted to the second upper storage electrode **154** through the initialization voltage line **192** has a predetermined negative (-) voltage, the second lower storage electrode **132** can be used as the conductor.

FIG. 8 is a graph showing a second storage capacitance depending on an initialization voltage applied to a second storage capacitor of an OLED display according to an exemplary embodiment of the present disclosure.

As shown in FIG. 8, when the initialization voltage V_{int} reaches about -3.5V, it can be confirmed that the second lower storage electrode **132** becomes the conductor, such that the second storage capacitance has a predetermined value.

As described above, the second storage capacitor **Cst2** stores the second storage capacitance corresponding to the difference between the initialization voltage V_{int} transmitted to the second upper storage electrode **132** through the initialization voltage line **192** and the compensation voltage $Dm+V_{th}$ transmitted to the second lower storage electrode **154** through the driving connecting member **174**. For example, since the gate insulating layer **140** with the thickness lower than the interlayer insulating layer **160** is used as the dielectric material of the second storage capacitor **Cst2**,

when it is assumed that the plane area of the second storage capacitor **Cst2** is the same as the plane area of the first storage capacitor **Cst1**, the second storage capacitance of the second storage capacitor **Cst2** is larger than the first storage capacitance of the first storage capacitor **Cst1**. Accordingly, the total storage capacitance of one pixel is maximized.

As described above, by forming the first storage capacitor **Cst1** and the second storage capacitor **Cst2** in one pixel, the storage capacitance can be maximized.

The data line **171** crosses the scan line **151** and extends in the column direction, and the driving voltage line **172** is separated from the data line **171** and extends in the column direction.

The light emission control connecting member (or light emission control connector) **179** having a substantially rectangular shape is connected to the pixel electrode **191** through the contact hole **81**, and the initialization connecting member **175** is connected to the initialization voltage line **192** through the contact hole **82**.

Hereinafter, the section structure of the OLED display according to the exemplary embodiment of the present disclosure will be described in detail according to the stacked order with reference to FIG. 5, FIG. 6, and FIG. 7.

In this case, the operation control transistor **T5** is substantially the same as the stacked structure of the light emission control transistor **T6** and therefore a detailed description thereof will be omitted.

A buffer layer **120** is formed on the substrate **110**. The substrate **110** can be formed as an insulating substrate, which is formed of glass, quartz, ceramic, plastic, or the like. The buffer layer **120** serves to block impurities from the substrate **110** in order to improve characteristics of polysilicon at the time of the crystallization process for forming polysilicon and planarizing the substrate **110** to mitigate stress of the semiconductor formed on the buffer layer **120**. The buffer layer **120** can be formed of silicon nitride ($SiNx$), silicon oxide (SiO_2), or the like.

A semiconductor **130** that includes a channel **131** including a driving channel **131a**, a switching channel **131b**, a compensation channel **131c**, an initialization channel **131d**, an operation control channel **131e**, a light emission control channel **131f**, and a bypass channel **131g**, and a semiconductor **130** that includes a second lower storage electrode **132** are formed on the buffer layer **120**. The driving source electrode **136a** and the driving drain electrode **137a** are formed at both sides of the driving channel **131a** of the semiconductor **130** and the switching source electrode **136b**, and the switching drain electrode **137b** is formed at both sides of the switching channel **131b**. Further, the compensation source electrode **136c** and the compensation drain electrode **137c** are formed at both sides of the compensation channel **131c** and the initialization source electrode **136d**, and the initialization drain electrode **137d** is formed at both sides of the initialization channel **131d**. Further, the operation control source electrode **136e** and the operation control drain electrode **137e** are formed at both sides of the operation control channel **131e** and the light emission control source electrode **136f**, and the light emission control drain electrode **137f** is formed at both sides of the light emission control channel **131f**. The bypass source electrode **136g** and the bypass drain electrode **137g** are formed at both sides of the bypass channel **131g**.

A gate insulating layer **140** covering the semiconductor **130** is formed thereon. Gate metal lines **151**, **152**, **153**, **158**, **155a**, and **154**, which include a scan line **151** including a switching gate electrode **155b** and a compensation gate electrode **155c**, a previous scan line **152** including an

initialization gate electrode **155d**, a light emission control line **153** including an operation control gate electrode **155e** and a light emission control gate electrode **155f**, a bypass control line **158** including a bypass gate electrode **155g**, a driving gate electrode (a first lower storage electrode) **155a**, and a second upper storage electrode **154**, are formed on the gate insulating layer **140**. The gate metal lines **151**, **152**, **153**, **158**, **155a**, and **154** can be formed in multiple layers in which metal layers formed of any one of copper (Cu), copper alloy, aluminum (Al), aluminum alloy, molybdenum (Mo), and molybdenum alloy are stacked.

An interlayer insulating layer **160** covering the gate metal layers **151**, **152**, **153**, **158**, **155a**, and **154**, and the gate insulating layer **140** is formed thereon. The interlayer insulating layer **160** can be formed of silicon nitride (SiNx) or silicon oxide (SiO₂).

The interlayer insulating layer **160** has contact holes **61**, **62**, **63**, **64**, **65**, **66**, **67**, **68**, and **69**. Metal data lines **171**, **172**, **174**, **175**, **176**, and **179**, which include a data line **171**, a driving voltage line **172** including a first upper storage electrode **178**, a driving connecting member **174**, an initialization connecting member **175**, a storage connecting member (or storage connector) **176**, and a light emission control connecting member **179**, are formed on the interlayer insulating layer **160**. The metal data lines **171**, **172**, **174**, **175**, **176**, and **179** can be formed in multiple layers, in which metal layers formed of any one of copper (Cu), copper alloy, aluminum (Al), aluminum alloy, molybdenum (Mo), and molybdenum alloy are stacked, and for example, can be formed of a triple layer of titanium/aluminum/titanium (Ti/Al/Ti), molybdenum/aluminum/molybdenum (Mo/Al/Mo), molybdenum/copper/molybdenum (Mo/Cu/Mo), or the like.

The data line **171** is connected to the switching source electrode **136b** through the contact hole **62** formed in the gate insulating layer **140** and the interlayer insulating layer **160**, and the first driving voltage line **172a** partially extends to form a first upper storage electrode **178**.

One end of the driving connecting member **174** is connected to the second lower storage electrode **132** through the contact hole **61** formed in the interlayer insulating layer **160**, and the other end of the driving connecting member **174** is connected to the compensation drain electrode **137c** and the initialization drain electrode **137d** through the contact hole **63** formed in the gate insulating layer **140** and the interlayer insulating layer **160**.

One end of the initialization connecting member **175** is connected to the initialization source electrode **136d** through the contact hole **64** formed in the gate insulating layer **140** and the interlayer insulating layer **160**, and the other end of the initialization connecting member **175** is connected to the second upper storage electrode **154** through the contact hole **67** formed in the interlayer insulating layer **160**.

The storage connecting member **176** connects the second lower storage electrode **132** and the first lower storage electrode **155a** to each other through the contact hole **67** formed in the gate insulating layer **140** and the interlayer insulating layer **160**. Accordingly, the second lower storage electrode **132** and the first lower storage electrode **155a** are applied with the compensation voltage $Dm+V_{th}$ through the driving connecting member **174**.

Also, the light emission control connecting member **179** is connected to the light emission drain electrode **137f** through the contact hole **66** formed in the gate insulating layer **140** and the interlayer insulating layer **160**.

A passivation layer **180** is formed on the metal data lines **171**, **172**, **174**, **175**, **176**, and **179** and the interlayer insulating layer **160**. The passivation layer **180** covers the metal

data lines **171**, **172**, **174**, **175**, **176**, and **179** to flatten them, such that the pixel electrode **191** can be formed on the passivation layer **180** without a step. The passivation layer **180** can be formed of a stacked layer of an organic material, such as polyacrylates resin, polyimides resin, or the like, or a stacked layer of an organic material and an inorganic material.

The pixel electrode **191** and an initialization voltage line **192** are formed on the passivation layer **180**. The light emission control connecting member **179** is connected to the pixel electrode **191** through the contact hole **81** formed in the passivation layer **180**, and the initialization connecting member **175** is connected to the initialization voltage line **192** through the contact hole **82** formed in the passivation layer **180**.

A pixel definition layer (PDL) **350** covering the passivation layer **180**, the initialization voltage line **192**, and the edge of the pixel electrode **191** is formed thereon, and the pixel definition layer **350** has a pixel opening **351** exposing the pixel electrode **191**. The pixel definition layer **350** can be formed of organic materials such as polyacrylates resin, polyimides resin, and the like, and silica-based organic materials.

An organic emission layer **370** is formed on the pixel electrode **191** exposed through the pixel opening **351** and a common electrode **270** is formed on the organic emission layer **370**. The common electrode **270** is also formed on the pixel definition layer **350** over the pixels PX. As such, the OLED (OLD) including the pixel electrode **191**, the organic emission layer **370**, and the common electrode **270** is formed.

Here, the pixel electrode **191** is an anode, which is a hole injection electrode, and the common electrode **270** is a cathode, which is an electron injection electrode. However, the exemplary embodiment according to the present disclosure is not necessarily limited thereto, and the pixel electrode **191** can be the cathode and the common electrode **270** can be the anode according to a driving method of the foldable display device. Holes and electrons are injected into the organic emission layer **370** from the pixel electrode **191** and the common electrode **270**, respectively, and excitons acquired by combining the injected holes and electrons fall from an excitation state to a ground state.

The organic emission layer **370** is formed of a low-molecular organic material or a high-molecular organic material such as poly(3,4-ethylenedioxythiophene) (PEDOT). Further, the organic emission layer **370** can be formed with multiple layers, including at least one of an emission layer, a hole injection layer (HIL), a hole transporting layer (HTL), an electron transporting layer (ETL), and an electron injection layer (EIL). When the organic emission layer **370** includes all of the layers, the hole injection layer is formed on the pixel electrode **191**, which is the positive electrode, and the hole transporting layer, the light emission layer, the electron transporting layer, and the electron injection layer are sequentially laminated thereon.

The organic emission layer **370** can include a red organic emission layer emitting red light, a green organic emission layer emitting green light, and a blue organic emission layer emitting blue light, and the red organic emission layer, the green organic emission layer, and the blue organic emission layer are formed at a red pixel, a green pixel, and a blue pixel, respectively, to implement color images.

Further, in the organic emission layer **370**, all of the red organic emission layer, the green organic emission layer, and the blue organic emission layer are laminated together on the red pixel, the green pixel, and the blue pixel, and a red color

filter, a green color filter, and a blue color filter are formed for each pixel to implement the color images. As another example, a white organic emission layer emitting white light is formed on all of the red pixel, the green pixel, and the blue pixel, and the red color filter, the green color filter, and the blue color filter are formed for each pixel to implement the color images. When the color images are implemented by using the white organic emission layer and the color filters, a deposition mask for depositing the red organic emission layer, the green organic emission layer, and the blue organic emission layer on individual pixels, i.e., the red pixel, the green pixel, and the blue pixel, may not be necessary.

The white organic emission layer described in another example can, of course, be formed by one organic emission layer, and even includes a configuration that can emit white light by laminating a plurality of organic emission layers. As an example, the white organic emission layer includes a configuration that enables the white light to be emitted by combining at least one yellow organic emission layer and at least one blue organic emission layer, a configuration that enables the white light to be emitted by combining at least one cyan organic emission layer and at least one red organic emission layer, a configuration that enables the white light to be emitted by combining at least one magenta organic emission layer and at least one green organic emission layer, and the like.

An encapsulation member (or encapsulator; not shown) protecting the OLED OLD can be formed on the common electrode 270, and the encapsulation member can be sealed to the substrate 110 by a sealant and can be formed of various materials, such as glass, quartz, ceramic, plastic, and a metal. On the other hand, a thin film encapsulation layer can be formed on the common electrode 270 by depositing the inorganic layer and the organic layer with the usage of the sealant.

While the inventive technology has been described in connection with what is presently considered to be practical exemplary embodiments, it is to be understood that the disclosure is not limited to the disclosed embodiments, but, on the contrary, is intended to cover various modifications and equivalent arrangements included within the spirit and scope of the appended claims.

What is claimed is:

1. An organic light-emitting diode (OLED) display, comprising:

- a substrate;
- a scan line formed over the substrate and configured to provide a scan signal;
- a data line crossing the scan line and configured to provide a data voltage;
- a driving voltage line crossing the scan line and configured to provide a driving voltage;
- a switching transistor electrically connected to the scan line and the data line;
- a driving transistor electrically connected to the switching transistor and including a driving gate electrode and a driving channel overlapping each other in a depth dimension of the OLED display;
- a first storage capacitor overlapping the driving channel in the depth dimension and including a first lower storage electrode and a portion of the driving voltage line;
- a second storage capacitor separated from the first storage capacitor, overlapping the portion of the driving voltage line in the depth dimension, and including a second lower storage electrode and a second upper storage electrode overlapping the second lower storage electrode in the depth dimension, wherein the second upper

storage electrode is formed on the same layer as the first lower storage electrode; and

an OLED electrically connected to the driving transistor.

2. The OLED display of claim 1, wherein the first lower storage electrode includes the driving gate electrode, and the first storage capacitor includes a first upper storage electrode overlapping the first lower storage electrode and including the portion of the driving voltage line.

3. The OLED display of claim 2, wherein the second lower storage electrode is formed on the same layer as the driving channel.

4. The OLED display of claim 3, wherein the first lower storage electrode and the second upper storage electrode are separated from each other.

5. The OLED display of claim 3, wherein the first lower storage electrode is formed on the same layer as the scan line.

6. The OLED display of claim 5, further comprising a storage connector formed on the same layer as the driving voltage line and configured to electrically connect the first lower storage electrode to the second lower storage electrode.

7. The OLED display of claim 6, wherein the OLED includes a pixel electrode electrically connected to the driving transistor, an organic emission layer formed over the pixel electrode, and a common electrode formed over the organic emission layer, and wherein the OLED display further comprises:

an initialization voltage line formed on the same layer as the pixel electrode and configured to provide an initialization voltage to initialize the driving transistor; and

an initialization connector configured to electrically connect the initialization voltage line to the second upper storage electrode.

8. The OLED display of claim 7, further comprising: a gate insulating layer formed over the substrate; and an interlayer insulating layer at least partially covering the first lower storage electrode and the second upper storage electrode formed over the gate insulating layer, wherein the storage connector and the initialization connector are formed over the interlayer insulating layer.

9. The OLED display of claim 7, wherein the storage connector has a contact hole configured to electrically connect the first lower storage electrode to the second lower storage electrode.

10. The OLED display of claim 8, wherein the gate insulating layer is thinner than the interlayer insulating layer.

11. The OLED display of claim 1, wherein the driving channel is formed over the substrate, and wherein the driving channel is non-linear.

12. The OLED display of claim 1, wherein the driving voltage line includes i) a first driving voltage line substantially parallel to the data line and ii) a second driving voltage line crossing the data line, wherein the first driving voltage line is formed on the same layer as the data line, and wherein the second driving voltage line is formed on the same layer as the scan line.

13. The OLED display of claim 1, wherein the first and second storage capacitors are spaced apart from each other within a pixel of the OLED display.

14. The OLED display of claim 1, wherein the driving transistor further includes a driving source electrode and a driving drain electrode located at opposing ends of the driving channel.

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15. The OLED display of claim 14, further comprising:
 a compensation transistor electrically connected to the driving drain electrode and configured to be turned on based on a scan signal so as to compensate a threshold voltage of the driving transistor; and
 a driving connector configured to electrically connect a compensation drain electrode of the compensation transistor to the driving gate electrode.

16. An organic light-emitting diode (OLED) display comprising:

a substrate;
 a data line formed over the substrate and configured to provide a data voltage;
 a driving voltage line formed adjacent to the data line and configured to provide a driving voltage;
 a first storage capacitor including a first upper storage electrode, wherein a portion of the driving voltage line is the first upper storage electrode; and
 a second storage capacitor electrically separated from the first storage capacitor and overlapping the portion of the driving voltage line in a depth dimension of the OLED display.

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17. The OLED display of claim 16, further comprising a driving transistor including a driving gate electrode and a driving channel overlapping each other in the depth dimension, wherein the first storage capacitor overlaps the driving channel in the depth dimension.

18. The OLED display of claim 17, wherein the first storage capacitor further includes a first lower storage electrode including the driving gate electrode, and wherein the second storage capacitor includes i) a second lower storage electrode formed on the same layer as the driving channel and ii) a second upper storage electrode overlapping the second lower storage electrode in the depth dimension and formed on the same layer as the first lower storage electrode.

19. The OLED display of claim 18, further comprising an OLED including a pixel electrode formed over the first upper and lower storage electrodes and the second upper and lower storage electrodes.

20. The OLED display of claim 19, wherein the first and second storage capacitors partially overlap each other.

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专利名称(译)	有机发光二极管显示器		
公开(公告)号	US10340324	公开(公告)日	2019-07-02
申请号	US15/138054	申请日	2016-04-25
[标]申请(专利权)人(译)	三星显示有限公司		
申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
[标]发明人	PYON CHANG SOO		
发明人	PYON, CHANG SOO		
IPC分类号	H01L27/32 G09G3/3233		
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外部链接	Espacenet		

摘要(译)

公开了一种有机发光二极管 (OLED) 显示器。在一个方面，显示器包括基板，形成在基板上方并配置为提供扫描信号的扫描线，以及与扫描线交叉并配置为提供数据电压的数据线。显示器还包括与扫描线交叉并配置为提供驱动电压的驱动电压线，电连接到扫描线和数据线的开关晶体管，以及电连接到开关晶体管并包括驱动栅电极的驱动晶体管以及在显示器的深度尺寸上彼此重叠的驱动通道。第一存储电容器在深度尺寸上与驱动沟道重叠并且包括驱动电压线的一部分。第二存储电容器与第一存储电容器分离并且与驱动电压线的一部分重叠。

